OVLFx3C7



Features:

- High brightness with well-defined spatial radiation patterns
- UV-resistant epoxy lens
- 30° Beam Angle



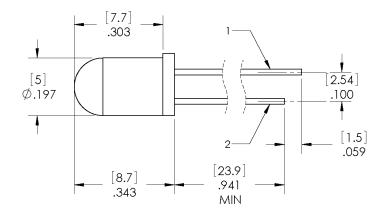
Description:

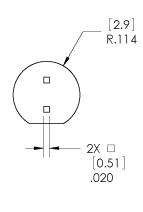
Each device in the OVLFx3C7 series is a high-intensity LED mounted in a clear plastic T-1¾ package. The LED provides a well-defined and even emission pattern. The UV-resistant epoxy lens makes this device an optimal solution for outdoor applications.

Applications:

- Traffic and pedestrian signals
- Signage and architectural lighting
- Backlighting
- Automotive

Part Number	Material	Emitted Color	Intensity Typ. mcd	Lens Color
OVLFB3C7	InGaN	Blue	5,200	Clear
OVLFG3C7	InGaN	Green	16,000	Clear
OVLFR3C7	AllnGaP	Red	7,400	Clear
OVLFY3C7	AllnGaP	Yellow	7,400	Clear









1 ANODE 2 CATHODE DIMENSIONS ARE IN INCHES AND [MILLIMETERS].

Leadframe material is iron alloy with tin-plated leads

DO NOT LOOK DIRECTLY AT LED WITH UNSHIELDED EYES OR DAMAGE TO RETINA MAY OCCUR.

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Electrical Specifications Absolute Maximum Ratings (T_A = 25° C unless otherwise noted)

— · · · · · · · · · · · · · · · · · · ·		
Storage Temperature Range		-40 ~ +100 °C
Operating Temperature Range		-40 ~ +100 °C
Reverse Voltage		5 V
Continuous Forward Current	Blue, Green	25 mA
Continuous Forward Current	Red, Yellow	50 mA
Peak Forward Current (10% Duty Cycle, 1 kHz)	Blue, Green	100 mA
Peak Forward Current (10% Duty Cycle, 1 kHz)	Red, Yellow	100 mA
Power Dissipation	Blue, Green	100 mW
Power Dissipation	Red, Yellow	120 mW
Current Linearity vs Ambient Temperature	Blue, Green	-0.29 mA/° C
Current Linearity vs Ambient Temperature	Red, Yellow	-0.72 mA/° C
Electrostatic Discharge Classification (JEDEC-JESD22-A114F)		Class 1C
LED Junction Temperature		125° C
Lead Soldering Temperature (4 mm from the base of the epoxy bulb)		260° C / 5 seconds

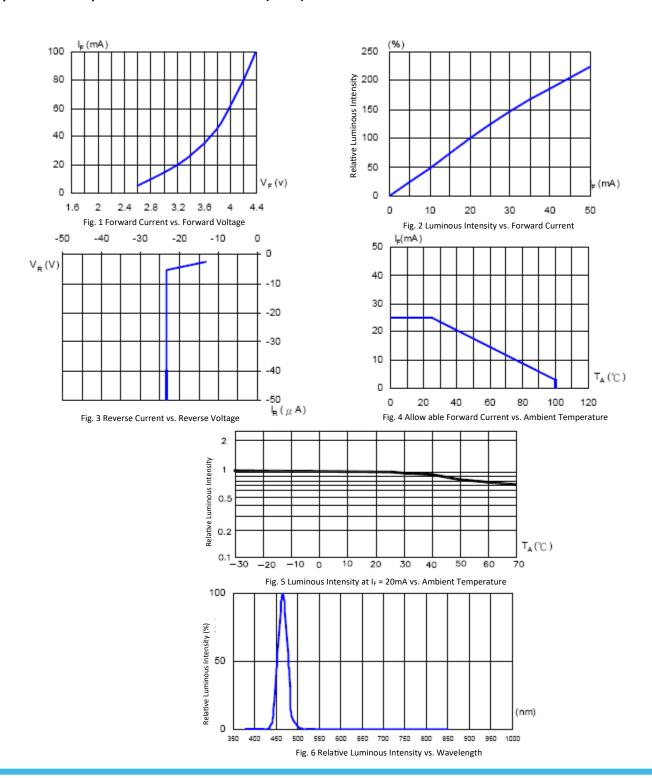
Electrical Characteristics $T_A = 25^{\circ} C$ unless otherwise noted

SYMBOL	PARAMETER	COLOR	MIN	TYP	MAX	UNITS	CONDITIONS	
	Luminous Intensity	Blue	3,115	5,200		mcd		
		Green	8,550	16,000			I _F = 20 mA	
I _V		Red	4,360	7,400			I _F = 20 IIIA	
		Yellow	4,360	7,400				
		Blue	2.6	3.4	4.0	· >	I _F = 20 mA	
V _F	Forward Voltage	Green						
V _F	Forward Voltage	Red	1 0	2.0	2.4			
		Yellow	1.8 w					
	Reverse Current	Blue			10	μА	V _R = 5 V	
1.		Green						
I _R		Red						
		Yellow						
	Dominant Wavelength	Blue	460	470	475	nm		
λ_{D}		Green	519	525	531		I _F = 20 mA	
ΛD		Red	620	623	630		1 _F – 20 111A	
		Yellow	585	589	595			
Δλ	Spectra Half Width	Blue		25		nm	I _F = 20 mA	
		Green						
		Red						
		Yellow						
20½H-H	50% Power Angle	· · · · · · · · · · · · · · · · · · ·		30		deg	I _F = 20 mA	

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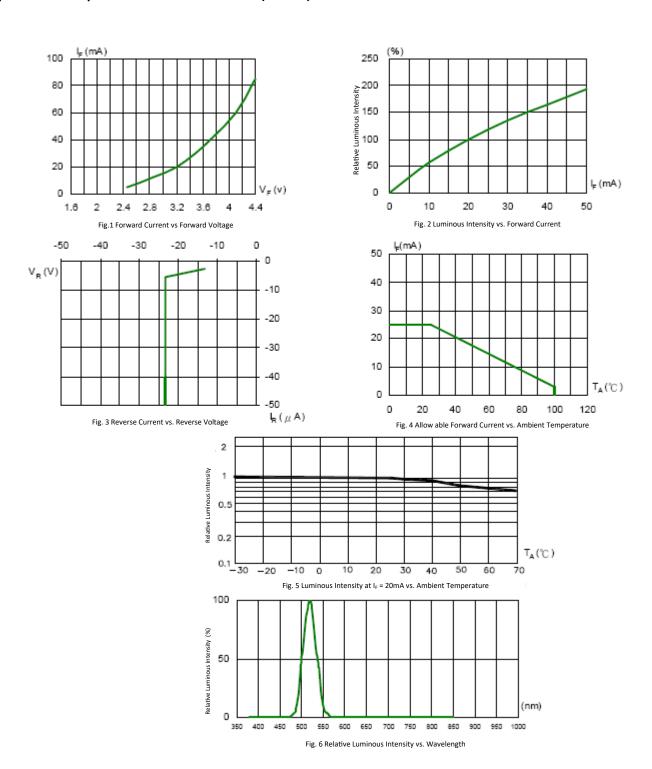
Typical Electro-Optical Characteristics Curves (BLUE)



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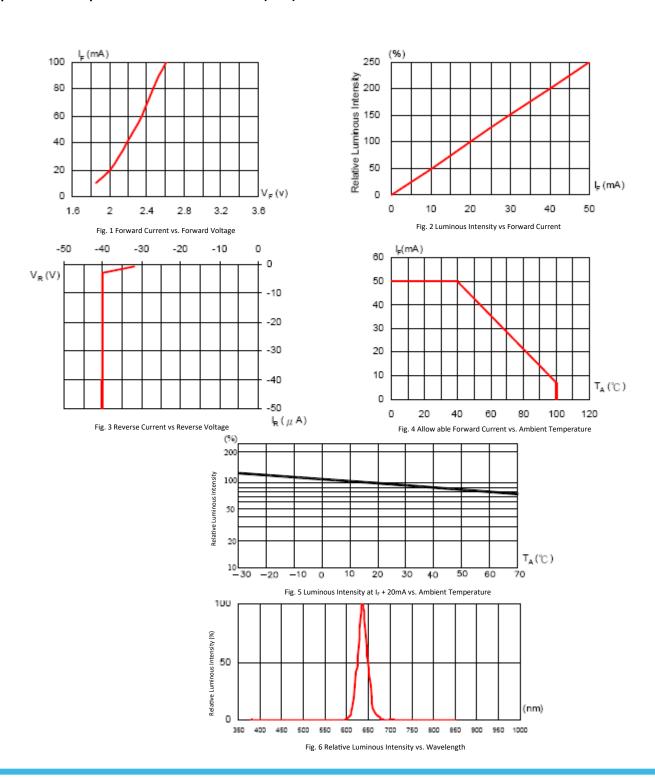
Typical Electro-Optical Characteristics Curves (GREEN)



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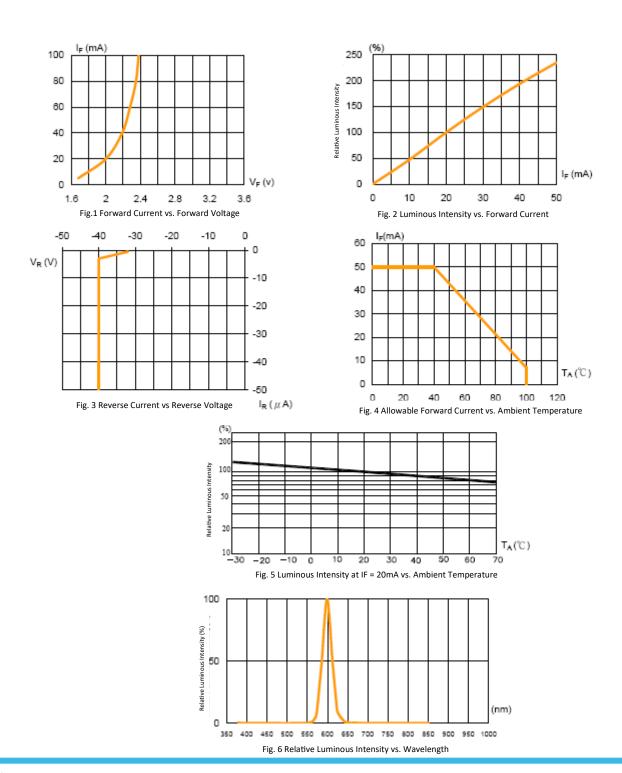
Typical Electro-Optical Characteristics Curves (RED)



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Typical Electro-Optical Characteristics Curves (YELLOW)

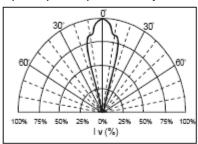


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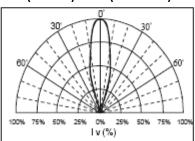


Beam Pattern

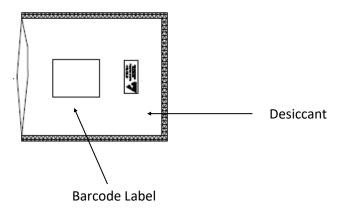
(RED) and (YELLOW)



(BLUE) and (GREEN)



Packaging: 500 pcs per bulk bag with desiccant



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Reliability Test

LED lamps are checked by reliability tests based on MIL standards.

Classi- fication	Test Item	Standard Test Method	Test Conditions	Duration	Unit	Acc / Rej Criteria	Result
Life Test	Operation Life Test (OLT)	MIL-STD-750D Method 1026.3	$T_A=25^{\circ}C$, $I_F=30\text{mA}$ *	1000 Hrs	100	0 / 1	Pass
Environment Test	High Temperature Storage (HTS)	MIL-STD-750D Method 1032.1	T _A =100°C	1000 Hrs	100	0 / 1	Pass
	Low Temperature Storage (LTS)	MIL-STD-750D Method 1032.1	$T_A = -40^{\circ}C$	1000 Hrs	100	0 / 1	Pass
	Temp. & Humidity with Bias (THB)	MIL-STD-750D Method 103B	$T_A=85^{\circ}C$, Rh=85% $I_F=20$ mA **	500 Hrs	100	0 / 1	Pass
	Thermal Shock Test (TST)	MIL-STD-750D Method 1056.1	0°C ~ 100°C 2min 2min	100 cycles	100	0 / 1	Pass
	Temperature Remark: (*) I _F :	MIL-STD-750D =30mA for AlinGaP	$-40^{\circ}\text{C} \sim 25^{\circ}\text{C} \sim 100^{\circ}\text{C} \sim 25^{\circ}\text{C}$ chip; $I_F = 20\text{mA}$ for InGaN chip	100	100	Λ/1	Dacc

(*) USL: Upper Standard Level , (**) LSL: Lower Standard Level

(**) IF =20mA for AlInGaP chip; IF =10mA for InGaN chip

2. Failure Criteria (T_A =25°C):

Test Item	Symbol	Test Conditions	Criteria for Judgment			
			Min.	Max.		
Luminous Intensity	$I_{ m V}$	I _F =20 mA	LSL×0.7 **			
Voltage (Forward)	V_{F}	I _F =20 mA		USL×1.1 *		

General Note

Mechanical Test